

**1. Scope :**

1-1. This specification applies to N channel silicon MOSFET chips,  
Device no. PM-0117A

**2. Structure :**

- 2-1. Planar type.
- 2-2. Electrodes.  
Source : Aluminum alloy .  
Gate : Aluminum alloy .  
Drain : Gold alloy.

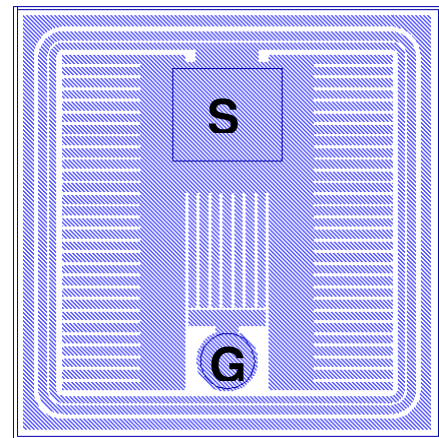
**3. Size :**

- 3-1. Chip size : 46.9 mils × 46.9 mils ( 1.190 mm × 1.190 mm ).
- 3-2. Chip thickness : 12 ± 1.5 mils ( 0.305 ± 0.038 mm ).
- 3-3. Pad size :  
Source : 12.0 mils × 10.0 mils ( 0.306 mm × 0.256 mm ).  
Gate : 5.9 mils × 5.9 mils ( 0.150 mm × 0.150 mm ).
- 3-4. Pattern drawing : Refer to the attached drawing.

**4. Absolute maximum rating (Ta = 25 °C)**

Parameter	Symbol	Rating	Unit
Continuous drain current V <sub>GS</sub> =5v	I <sub>D(m)</sub>	0.4	A
Drain-source Voltage	V <sub>DSS</sub>	250	V
Gate-source Voltage	V <sub>GS</sub>	±10	V
Operating junction and storage temperature range	T <sub>J</sub> T <sub>STG</sub>	-40to+150	°C

Pattern drawing



**5. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain to source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V I <sub>D</sub> = 100uA	250			V
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 1mA	1.0	1.8	3.0	V
Gate to source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V V <sub>DS</sub> = 0V		± 0.07	± 1	μA
Drain to source leakage current	I <sub>DSS</sub>	V <sub>GS</sub> = 0V V <sub>DS</sub> = 250V			1	μA
Drain to source on resistance	R <sub>DSS(on)</sub>	V <sub>GS</sub> = 5V I <sub>D</sub> = 100mA		4	4.5	Ω
Diode forward voltage drop	V <sub>SD</sub>	V <sub>GS</sub> = 0V I <sub>SD</sub> = 100mA		0.84	1.8	V

